



#12/Amdt B
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C.P.

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Cathi H. Turner

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PATENT

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

In re Application of: Cuomo et al.

Group Art Unit: 2818

Serial No.: 09/998,080

Examiner: Nhu, David

Filed: November 30, 2001

Docket No.: 297/105/2

Confirmation No.: 4519

For: M^{III}N BASED MATERIALS AND METHOD AND APPARATUS
PRODUCING SAME

AMENDMENT B

Commissioner for Patents
Washington, D.C. 20231

Sir:

This is responsive to the Office Action dated December 18, 2002, Paper No. 11, having a term that will expire on March 18, 2003. Favorable consideration is respectfully requested in view of the following Amendments and Remarks.

AMENDMENT

Please amend the subject application as follows:

IN THE SPECIFICATION:

Please amend the specification as follows:

On page 6, lines 13 – 22, please replace the existing paragraph with the following paragraph:

— According to one method of the present invention, a single-crystal M^{III}N article is produced. A template material having an epitaxial-initiating growth surface is provided. A Group III metal target is sputtered in a plasma-enhanced environment to produce a Group III metal source vapor. The Group III metal source vapor is combined with a nitrogen-containing gas to produce